## AMENDMENTS TO THE SPECIFICATION

Please amend the specification by rewriting the following paragraphs, as set forth below in marked-up form.

Please amend the paragraph beginning on page 1, line 25 and continuing onto page 2, with the following amended paragraph:

Fig. 13 is an input/output characteristic diagram showing the relationship between the ~~light~~ amount of light incident to an image pickup device and the output signal amount thereof. Apparent from the input/output characteristic diagram, the dynamic range of the image pickup device is determined by the saturated signal amount of each pixel and the noise level.

Please amend the paragraph beginning on page 12, line 8, with the following amended paragraph:

The first vertical scan pulse $\varphi V1n$ and the second vertical scan pulse $\varphi V2n+i$ are output from the first vertical scan circuit 30 and the second vertical scan circuit 31 respectively at a time t1 by the vertical scan operation of the first and second vertical scan circuits 30, 31. The first vertical scan pulse $\varphi V1n$ is applied through the vertical selection line 34n to the gate of the vertical selection transistor 27n on the n-th row, and the second vertical scan pulse $\varphi V2n+i$ is applied through the vertical selection line 36n+i to the gate of the vertical selection transistor 28n+i on the (n+i)-th row. As a result, the n-th row, the (n+~~i~~i)-th row are selected.

Please amend the paragraph beginning on page 16, line 3, with the following amended paragraph:

Accordingly, the signal corresponding to the charge amount of charges which are photoelectrically converted and accumulated in the photodiode 12 for the accumulation time of t2 - t1 (that is, a long-time accumulation signal) at each pixel of the n-th row is output as an output OUT 2 through the horizontal signal line 22n of the n-th row ~~a~~through the vertical selection transistor 28n ~~a~~through the second vertical signal line 26. Since the signal is also read out from the photodiode 12 at this time point, the photodiode 12 is reset.

Please amend the paragraph beginning on page 16, line 25 and continuing onto page 17, with the following amended paragraph:

Accordingly, in each pixel of the n-th row, the signal corresponding to the charge amount of charges which are photoelectrically converted and accumulated for the accumulation time of t3 - t2 (that is, a short-time accumulation signal) in the photodiode 12 is output as an output OUT 1 through the horizontal signal line 22n of the n-th row 3-through the vertical selection transistor 27n 3 through the first vertical signal line 26.

Please amend the paragraph beginning on page 25, line 16, with the following amended paragraph:

In this case, the high-speed image pickup operation of the CMOS image pickup device in which the vertical signal lines, the vertical selection transistors and the vertical scan circuits are provided for two systems is described. However, if the number of systems may be increased to three systems, four systems, etc., the information of all the pixels can be picked up in one-third time, one-fourth time, etc., and thus the-higher-speed image pickup operation can be implemented.

Please amend the paragraph beginning on page 25, line 26 and continuing onto page 26, with the following amended paragraph:

In order to fabricate the CMOS image pickup device which can support only the-high-speed image pickup operation, if vertical start pulses of n are given to the vertical scan circuit to perform the vertical scan operation while skipping every (n-1) rows, only one vertical scan circuit is sufficient although the vertical selection transistors and the vertical signal lines of n systems are provided.

Please amend the paragraph beginning on page 26, line 18 and continuing onto page 27, with the following amended paragraph:

As described above, according to the present invention, in the solid-state image pickup device designed so that the signal corresponding to the accumulated charge amount of each pixel is

output to the horizontal signal lines wired on a row basis and the ~~cameral~~ camera system using the solid-state image pickup device as an image pickup device, plural vertical signal lines are provided in connection with each horizontal signal lines, and plural systems of vertical driving systems are disposed in connection with the vertical signal lines, whereby plural signals which are different in accumulation time and obtained by dividing 1 field into any number of parts with any integer times of 1H can be separately output, so that the broad dynamic range image pickup operation can be implemented without inducing any vertically striped system noise.